6-OUTPUT LOW-POWER DIFFERENTIAL SYNTHESIZER FOR PCIE GEN1/2/3

9FGL639

Description

The 9FGL639 is a 6-output low-power clock sythesizer for PCIe Gen1/2/3. It runs from a 25MHz XTAL, provides spread spectrum capability, and has an SMBus for software control of the device.

Recommended Application

6 - Output Low-Power Differential Synthesizer for PCIe Gen1/2/3

Output Features

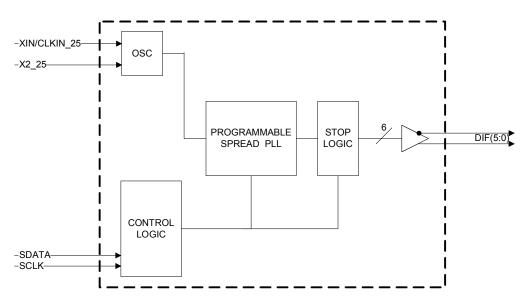
• 6 - Differential low power push pull HCSL-compatible (LP-HCSL) output pairs

Features/Benefits

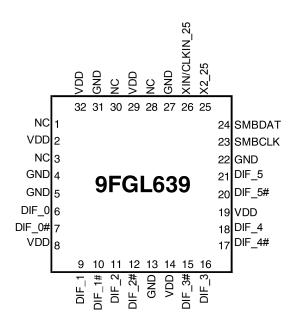
- 32-pin QFN; Space-savings
- LP-HCSL outputs/Low power consumption, reduced component count
- PCIe Gen1/2/3 /Supports latest systems
- Spread Spectrum Capability; reduced EMI when needed
- D2/D3 SMBus Write/Read SMBus address

Key Specifications

- Cycle-to-cycle jitter <50ps
- Output-to-output skew <100 ps
- Current consumption < 50mA
- PCIe Gen2 phase jitter <3.0ps RMS
- PCIe Gen3 phase jitter <1.0ps RMS



Block Diagram



Power Management

OE# (SMBUS)	Differential Outputs
1	DIF/DIF# = running
0	DIF/DIF# = Low/Low

Pin#	Pin Name	Туре	Pin Description
1	NC	N/A	No Connection.
2	VDD	PWR	Power supply, nominal 3.3V
3	NC	N/A	No Connection.
4	GND	PWR	Ground pin.
5	GND	PWR	Ground pin.
6	DIF_0		0.7V differential true clock output
7	DIF_0#	OUT	0.7V differential Complementary clock output
8	VDD	PWR	Power supply, nominal 3.3V
9	DIF_1	OUT	0.7V differential true clock output
10	DIF_1#	OUT	0.7V differential Complementary clock output
11	DIF_2	OUT	0.7V differential true clock output
12	DIF_2#		0.7V differential Complementary clock output
13	GND		Ground pin.
14	VDD	PWR	Power supply, nominal 3.3V
15	DIF_3#	OUT	0.7V differential Complementary clock output
16	DIF_3		0.7V differential true clock output
17	DIF_4#	OUT	0.7V differential Complementary clock output
18	DIF_4		0.7V differential true clock output
19	VDD		Power supply, nominal 3.3V
20	DIF_5#	OUT	0.7V differential Complementary clock output
21	DIF_5	OUT	0.7V differential true clock output
22	GND	PWR	Ground pin.
23	SMBCLK	IN	Clock pin of SMBUS circuitry, 5V tolerant
24	SMBDAT	I/O	Data pin of SMBUS circuitry, 5V tolerant
25	X2_25	OUT	Crystal output, Nominally 25.00MHz.
26	XIN/CLKIN_25	IN	Crystal input or Reference Clock input. Nominally 25MHz.
27	GND	PWR	Ground pin.
28	NC	N/A	No Connection.
29	VDD	PWR	Power supply, nominal 3.3V
30	NC	N/A	No Connection.
31	GND	PWR	Ground pin.
32	VDD	PWR	Power supply, nominal 3.3V

How to Write

- Controller (host) sends a start bit
- Controller (host) sends the write address
- IDT clock will **acknowledge**
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) sends the byte count = X
- IDT clock will acknowledge
- Controller (host) starts sending Byte N through Byte N+X-1
- IDT clock will acknowledge each byte one at a time

Index Block Write Operation

Controller (host) sends a Stop bit

How to Read

- Controller (host) will send a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- · Controller (host) will send a separate start bit
- · Controller (host) sends the read address
- IDT clock will acknowledge
- IDT clock will send the data byte count = X
- IDT clock sends Byte N+X-1
- IDT clock sends Byte 0 through Byte X (if X_(H) was written to Byte 8)
- Controller (host) will need to acknowledge each byte
- Controller (host) will send a not acknowledge bit
- Controller (host) will send a stop bit

Co	ntroller (Host)		IDT (Slave/Receiver)
Т	starT bit	-	
S	lave Address	-	
WR	WRite	-	
			ACK
Beg	inning Byte = N		
			ACK
RT	Repeat starT		
S	lave Address		
RD	ReaD		
			ACK
			Data Byte Count=X
	ACK		
			Beginning Byte N
	ACK		
		fe	0
	0	X Byte	0
	0		0
	0	4	
			Byte N + X - 1
Ν	Not acknowledge	-	
Р	stoP bit		

	Index Bl	ock W	rite Operation
Control	ler (Host)		IDT (Slave/Receiver)
Т	starT bit		
Slave	Address		
WR	WRite		
			ACK
Beginnin	g Byte = N		
			ACK
Data Byte	e Count = X		
			ACK
Beginnii	ng Byte N		
			ACK
0		×	
0		X Byte	0
0		Ö	0
			0
Byte N	I + X - 1		
			ACK
Р	stoP bit		

Read Address	Write Address
D2 _(H)	D3 _(H)

SMBus Table: Device Control Register, READ/WRITE ADDRESS (D2/D3)

Byt	te O	Pin #	Name	Control Function	Туре	0	1	Default
Bit 7		-	Reserved				0	
Bit 6		-		Reserved				
Bit 5			Spre	Spread Enable RW Off -0.50%			1	
Bit 4		-		Reserved				0
Bit 3		-		Reserv	ed			0
Bit 2		-		Reserved				0
Bit 1		-	Р				0	
Bit 0		-		Reserv	ed			0

SMBus Table: Output Enable Register

Byt	Byte 1 Pin #		Name	Control Function	Туре	0	1	Default
Bit 7	-			Reserv	ed			0
Bit 6	-		DIF_0 EN	Output Enable	RW	Disable	Enable	1
Bit 5	-			Reserved				0
Bit 4	-			Reserved				
Bit 3	-		DIF_1 EN	Output Enable	RW	Disable	Enable	1
Bit 2	-			Reserv	ed			0
Bit 1	-			Reserved				
Bit 0	-			Reserv	ed			0

SMBus Table: Reserved Register

Byt	te 2	Pin #	Name	Control Function	Туре	0	1	Default
Bit 7	-			Reserved				0
Bit 6	-		Reserved					0
Bit 5	-			Reserved				
Bit 4	-			Reserved				0
Bit 3	-			Reserve	ed			0
Bit 2	-			Reserved				0
Bit 1	-		Reserved				0	
Bit 0	-			Reserve	ed			0

SMBus Table: Output Enable Register

Byt	e 3	Pin #	Name	Control Function	Туре	0	1	Default
Bit 7	-	-	DIF_5 EN	Output Enable	RW	Disable	Enable	1
Bit 6	-	-	DIF_4 EN	Output Enable	RW	Disable	Enable	1
Bit 5	-	-		Reserved				0
Bit 4	-	-		Reserved				0
Bit 3	-	-		Reserv	ed			0
Bit 2	-	-		Reserved				0
Bit 1	-	-	Reserved				0	
Bit 0	-	-		Reserv	ed			0

SMBus Table: Reserved Register

Byt	e 4	Pin #	Name	Control Function	Туре	0	1	Default
Bit 7		-		Reserv	ed			0
Bit 6		-	Reserved					
Bit 5		-		Reserved				
Bit 4		-		Reserved				0
Bit 3		-		Reserv	ed			0
Bit 2		-		Reserv	ed			0
Bit 1		-	Reserved					0
Bit 0		-		Reserv	ed			0

SMBus Table: Output amplitude adjustment

Byt	te 5	Pin #	Name	Control Function	Туре	0	1	Default
Bit 7		-	DIF 5/6 AMP	Amplitude adjustment	RW		00=700mV 01=800mV	
Bit 6		-			RW	10=900mV 11=1000mV		1
Bit 5		-	DIF 1/2/3 AMP	Amplitude adjustment	RW		00mV 00mV	0
Bit 4		-		Amplitude adjustment	RW		00mV 00mV	1
Bit 3		-		Reserve	ed			0
Bit 2		-		Reserve	ed			0
Bit 1		-	DIF_0 AMP	Amplitude adjustment	RW	01=8	00mV 00mV	0
Bit 0		-			RW		00mV 00mV	1

SMBus Table: Reserved Register

Byt	te 6	Pin #	Name	Control Function	Туре	0	1	Default
Bit 7	-			Reserved				
Bit 6	-		Reserved					
Bit 5	-		Reserved					0
Bit 4	-			Reserved				0
Bit 3	-			Reserve	ed			0
Bit 2	-			Reserve	ed			0
Bit 1	-		Reserved				0	
Bit 0	-			Reserve	ed			0

SMBus Table: Vendor & Revision ID Register

Byt	te 7	Pin #	Name	Control Function	Туре	0	1	Default
Bit 7		-	RID3		R	-	-	0
Bit 6		-	RID2	REVISION ID	R	-	-	0
Bit 5		-	RID1		R	-	-	0
Bit 4		-	RID0		R	-	-	0
Bit 3		-	VID3		R	-	-	0
Bit 2		-	VID2	VENDOR ID	R	-	-	0
Bit 1		-	VID1		R	-	-	0
Bit 0		-	VID0		R	-	-	1
) T ® 6-OU	TPUT LO	W-POWER	DIFFERENTIAL SYNT	HESIZER FOR PCIE GEN1/2/3	6	-	9FGL639	REV A

SMBus Table: Reserved Register

Byt	te 8	Pin #	Name	Control Function	Туре	0	1	Default				
Bit 7				Reserved								
Bit 6				Reserved								
Bit 5				Reserved								
Bit 4				Reserved								
Bit 3				Reserved								
Bit 2				Reserv	ed			1				
Bit 1				Reserved								
Bit 0				Reserved								

SMBus Table: Output Enable Register

Byt	e 9	e 9 Pin # Name		Control Function	Туре	0	1	Default			
Bit 7				Reserved							
Bit 6	- C		DIF_3 EN	Output Enable	RW	Disable	Enable	1			
Bit 5	-		DIF_2 EN	Output Enable	RW	Disable	Enable	1			
Bit 4				Reserved							
Bit 3				Reserv	ed			0			
Bit 2				Reserv	ed			0			
Bit 1			Reserved								
Bit 0				Reserv	ed			0			



Stresses above the ratings listed below can cause permanent damage to the 9FGL639. These ratings, which are standard values for IDT commercially rated parts, are stress ratings only. Functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods can affect product reliability. Electrical parameters are guaranteed only over the recommended operating temperature range.

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	МАХ	UNITS	NOTES
3.3V Logic Supply Voltage	VDD				4.6	V	1,2
Input Low Voltage	V _{IL}		GND-0.5			V	1
Input High Voltage	V _{IH}	Except for SMBus interface			V_{DD} +0.5V	V	1
Input High Voltage	VIHSMB	SMBus clock and data pins			5.5V	V	1
Storage Temperature	Ts		-65		150	°C	1
Junction Temperature	Tj				125	°C	1
Input ESD protection	ESD prot	Human Body Model	Р			V	1

¹Guaranteed by design and characterization, not 100% tested in production.

² Operation under these conditions is neither implied nor guaranteed.

Electrical Characteristics–Input/Supply/Common Output Parameters

TA = T_{COM} : Supply Voltage VDD = 3.3 V +/-5%

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Ambient Operating Temperature	Т _{СОМ}	Commmercial range	0		70	°C	1
Input Frequency	F _{in}	X1 pin		25.000		MHz	1
Pin Inductance	L _{pin}				7	nH	1
	C _{IN}	Logic Inputs	1.5		5	pF	1
Capacitance	CINXTAL	Crystal inputs			6	pF	1
	C _{OUT}	Output pin capacitance			6	pF	1
Clk Stabilization	T _{STAB}	From V _{DD} Power-Up and after input clock stabilization to 1st clock		0.356	1.8	ms	1,2
SS Modulation Frequency	f _{MODIN}	Allowable Frequency (Triangular Modulation)	30	31.500	33	kHz	1
Tfall	t _F	Fall time of control inputs			5	ns	1,2
Trise	t _R	Rise time of control inputs			5	ns	1,2
SMBus Input Low Voltage	VILSMB				0.8	V	1
SMBus Input High Voltage	VIHSMB		2.1		V _{DDSMB}	V	1
SMBus Output Low Voltage	V _{OLSMB}	@ I _{PULLUP}			0.4	V	1
SMBus Sink Current	I _{PULLUP}	@ V _{OL}	4			mA	1
Nominal Bus Voltage	V _{DDSMB}	3V to 5V +/- 10%	2.7		5.5	V	1
SCLK/SDATA Rise Time	t _{RSMB}	(Max VIL - 0.15) to (Min VIH + 0.15)			1000	ns	1
SCLK/SDATA Fall Time	t _{FSMB}	(Min VIH + 0.15) to (Max VIL - 0.15)			300	ns	1
SMBus Operating Frequency	f _{MAXSMB}	Maximum SMBus operating frequency			100	kHz	1

¹Guaranteed by design and characterization, not 100% tested in production.

²Control input must be monotonic from 20% to 80% of input swing.

$T_A = T_{COM}$; Supply Voltage VDD = 3.3 V +/-5%, See Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES				
Slew rate	Trf	Scope averaging on	1	3	4	V/ns	1, 2, 3				
Slew rate matching	ΔTrf	Slew rate matching, Scope averaging on		5	20	%	1, 2, 4				
Voltage High	VHigh	Statistical measurement on single-ended signal using oscilloscope math function. (Scope	660	914	850	mV	1				
Voltage Low	VLow	averaging on)		-8	150	iii v	1				
Max Voltage	Vmax	Measurement on single ended signal using		937	1150	mV	1				
Min Voltage	Vmin	absolute value. (Scope averaging off)	Р	-42			1				
Vswing	Vswing	Scope averaging off	300			mV	1, 2				
Crossing Voltage (abs)	Vcross_abs	Scope averaging off	300	510	550	mV	1, 5				
Crossing Voltage (var)	∆-Vcross	Scope averaging off		18	140	mV	1, 6				

¹ Guaranteed by design and characterization, not 100% tested in production. $C_L = 2pF$ with $R_S = 33\Omega$ for $Zo = 50\Omega$ (100 Ω differential trace impedance).

² Measured from differential waveform

³ Slew rate is measured through the Vswing voltage range centered around differential 0V. This results in a +/-150mV window around differential 0V.

⁴ Matching applies to rising edge rate of Clock / falling edge rate of Clock#. It is measured in a +/-75mV window centered on the average cross point where Clock rising meets Clock# falling. The median cross point is used to calculate the voltage thresholds the oscilloscope uses for the edge rate calculations.

⁵ Vcross is defined as voltage where Clock = Clock# measured on a component test board and only applies to the differential rising edge (i.e. Clock rising and Clock# falling).

⁶ The total variation of all Vcross measurements in any particular system. Note that this is a subset of V_cross_min/max (V_cross absolute) allowed. The intent is to limit Vcross induced modulation by setting V_cross_delta to be smaller than V_cross abs.

Electrical Characteristics–Current Consumption

TA = T_{COM} . Supply Voltage VDD = 3.3 V +/-5%, See Test Loads for loading conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Operating Supply Current I _{DD3.3}		VDD, All outputs active @100MHz		41	50	mA	1

¹Guaranteed by design and characterization, not 100% tested in production.

Electrical Characteristics–Output Duty Cycle, Jitter, and Skew Characteristics

TA = T_{COM:} Supply Voltage VDD = 3.3 V +/-5%, See Test Loads for Loading Conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Duty Cycle	t _{DC}	Measured differentially, PLL Mode	45	50.3	55	%	1
Skew, Output to Output	t _{sk3}	V _T = 50%		29	100	ps	1
Jitter, Cycle to cycle	t _{jcyc-cyc}	PLL mode		29	50	ps	1,3

¹Guaranteed by design and characterization, not 100% tested in production.

³ Measured from differential waveform

TA = T_{COM} ; Supply Voltage VDD = 3.3 V +/-5%, See Test Loads for loading conditions

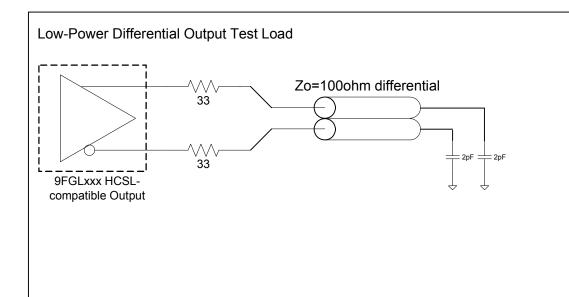
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	Notes
	t _{jphPCleG1}	PCIe Gen 1		29.4	86	ps (p-p)	1,2,3,6
	t _{jphPCleG2}	PCIe Gen 2 Lo Band		1.4		ps	1,2,6
		10kHz < f < 1.5MHz	1.4		3	(rms)	1,2,0
Phase Jitter, PCI Express		PCIe Gen 2 High Band	1.8		3.1	ps	1,2,6
Thase offici, T of Express		1.5MHz < f < Nyquist (50MHz)				(rms)	1,2,0
		PCIe Gen 3	0.45		1		1045
		(PLL BW of 2MHz-4MHz or 2MHz-5MHz,				ps (rma)	1,2,4,5, 6
		CDR = 10MHz)				(rms)	0

¹ Guaranteed by design and characterization, not 100% tested in production.

² See http://www.pcisig.com for complete specs

³ Sample size of at least 100K cycles. This figures extrapolates to 108ps pk-pk @ 1M cycles for a BER of 1-12.

⁶ Applies to all differential outputs



Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Thermal Resistance Junction to	θ _{JA}	Still air		34		° C/W
Ambient	θ _{JA}	1 m/s air flow		29		° C/W
	θ _{JA}	3 m/s air flow		27		° C/W
Thermal Resistance Junction to Case	θ _{JC}			32		° C/W

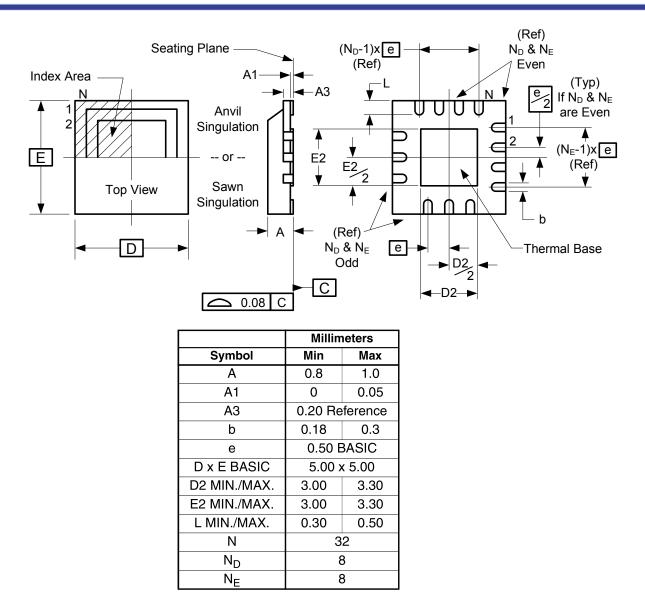
Marking Diagram



Notes:

- 1. Line 2: truncated part number
- 2. "L" denotes RoHS compliant package.
- 3. 'YYWW' is the last two digits of the year and week that the part was assembled.
- 4. 'COO' denotes country of origin.
- 5. 'LOT' deontes lot number.





Ordering Information

Part / Order Number	Marking	Shipping Packaging	Package	Temperature
9FGL639AKLF	see page 11	Trays	32-pin MLF	0 to +70° C
9FGL639AKLFT		Tape and Reel	32-pin MLF	0 to +70° C

"LF" suffix to the part number are the Pb-Free configuration, RoHS compliant.

"A" is the device revision designator (will not correlate with the datasheet revision).

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Rev.	Issue Date	WHO	Description	Page #
0.1	09/26/11	RDW	Initial Release	-
A	06/13/12	RDW	 Updated Gen-des and data sheet titles Updated electrical tables with characterization data Changed all references of PCIe to PCIe Gen1/2/3. Added LP-HCSL nomenclature Move to final and post to web. 	Various



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